What is claimed is:

1

	1	1. A method of fabricating a piezoelectric film having a patterned electrode of	leposited on a
	2	substrate, the electrode having an edge with a height, comprising the	
	3	reducing or eliminating the height of the edge, wherein a weakening	
The states states at the state of the state	4	edge is diminished.	
	1	2. The method of claim 1, wherein the piezoelectric film is selected from the	group
	2	consisting of:	
	3	a) aluminum nitride; and	
	4	b) zinc oxide.	
	1	3. The method of claim 1, wherein the patterned electrode is selected from the	ne groun
	2	consisting of aluminum and titanium.	o Sroup
	1	4. The method of claim 1 wherein the substrate is selected from the group co	nsisting of
	2	silicon and gallium arsenide.	
	1	The method of claim 1, wherein the step of reducing or eliminating the he	ght of the
The Am	2	edge comprises the substeps of:	
	3	a) depositing a non-conducting layer on the patterned electrode and th	e
	4	substrate; and	
	5	b) planarizing the non-conducting layer such that the non-conducting	ayer
	6	is of a same height as the patterned electrode.	·
	1	. The method of claim 5, wherein substep (b) is achieved using chemical me	chanical
	2	polishing.	
	1	The method of claim 5, wherein substep (b) is achieved using polymer plan	narization.
	1	The method of claim 5, wherein step (b) is achieved using reflow and lift-or	iff.

9. The method of claim 5, wherein the non-conducting layer has a low dielectric constant.

	1	10. The method of claim 5, wherein the non-conducting layer is SiO ₂ .
	1	11. The method of claim 1, wherein the step of reducing or eliminating the height of the
	2	edge results in a stair-step shaped electrode.
	1	12. The method of claim 11, wherein the step of reducing or eliminating the height of the
	2	edge comprises the substeps of:
	3	a) depositing a plurality of conducting layers on the substrate wherein
	4	alternate layers are composed of a first conducting material and
	5	adjacent layers are composed of a conducting material which is
	6	different from the first conducting material such that adjacent layers
	7	have a different etch profile from each other;
	8	b) selectively laterally etching a first conducting layer;
Aut time time Hu	9	c) selectively laterally etching a second conducting layer directly below
	10	said first conducting layer; and
	11	d) stopping step (c) at a point where said second conducting layer is etched
	12	less than said first conducting layer; and
The state of the s	13	e) repeating steps (b) through (d) for any additional conducting layers;
	14	such that a stair-step electrode is formed.
	1	13. The method of claim 12, wherein said alternating conducting layers are composed of
	2	titanium and aluminum.
	1	14. The method of claim 1, wherein the step of reducing or eliminating the height of the
	2	edge results in a dome-shaped electrode.
	1	15. The method of claim 14, wherein the step of reducing or eliminating the height of the
	2	edge comprises the substeps of:
	3	a) depositing a resist layer on an electrode layer;
	4	b) shaping said resist layer into a dome-shaped drop; and

	5	c) etching the resist layer and the electrode layer until said electrode layer is
	6	shaped like a dome.
	1	16. The method of claim 1, wherein the step of reducing or eliminating the height of the
	2	edge comprises the substeps of:
	3	a) depositing a non-conducting layer on the substrate;
	4	b) patterning the non-conducting layer such that a pattern of said non-
	5	conducting material is identical to a pattern desired for the
	6	electrode;
	7	c) depositing a plurality of layers on said non-conducting layer;
	8	d) depositing a masking film on a backside of the substrate;
	9	e) patterning the masking film;
11 200		f) etching the backside of the substrate until the non-conducting layer is
	11	reached; and
ladk SEE	12	g) etching a portion of the conducting layers which are not masked by the
4 14	13	non-conducting layer.
	1	17. The method of claim 16, wherein the non-conducting layer has a low dielectric
	2	constant.
	1	18. The method of claim 16, wherein the non-conducting layer is SiO ₂ .